AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1-2. Cancelled.

3. (Currently Amended) A high withstand voltage field effect type semiconductor device ~~according to claim 1~~ comprising:

a body region arranged in a semiconductor substrate;

a gate electrode facing to the body region;

a drift region arranged below the body region in the semiconductor substrate, the drift region having a conduction type opposite to that of the body region;

a field dispersion region arranged between the body region and the drift region, the field dispersion region having a conduction type which is the same as that of the drift region and having a low net impurity concentration; and

~~further comprising~~ emitter regions arranged discretely at an opposite side of the drift region, with the body region arranged between the emitter regions and the drift region, the emitter regions ~~being in~~ having a conduction type opposite to that of the body region[[,]]; and

wherein field dispersion regions are arranged discretely corresponding to the emitter regions.

4. (Currently Amended) A high withstand voltage field effect type semiconductor device ~~according to claim 2~~ comprising:

a body region arranged in a semiconductor substrate;

a gate electrode facing to the body region;

a drift region arranged below the body region in the semiconductor substrate, the drift region having a conduction type opposite to that of the body region;

a field dispersion region arranged between the body region and the drift region, the field dispersion region having a conduction type which is the same as that of the drift region and having a low net impurity concentration; and

~~further comprising~~ emitter regions arranged discretely at an opposite side of the drift region, with the body region arranged between the emitter regions and the drift region, the emitter regions ~~being in~~ having a conduction type opposite to that of the body region, ~~and~~

wherein field dispersion regions are arranged discretely corresponding to the emitter regions;

wherein the gate electrode is trench-structured; and

wherein the field dispersion region is formed extending to a bottom of the gate electrode.

5. (Currently Amended) A high withstand voltage field effect type semiconductor device ~~according to claim 1 further~~ comprising:

a body region arranged in a semiconductor substrate;

a gate electrode facing to the body region;

a drift region arranged below the body region in the semiconductor substrate, the drift region having a conduction type opposite to that of the body region;

a field dispersion region arranged between the body region and the drift region, the field dispersion region having a conduction type which is the same as that of the drift region and having a low net impurity concentration;

a buffer region arranged at an opposite side of the body region with the drift region arranged between the buffer region and the body region, the buffer region ~~being in~~ having a same conduction type ~~same~~ as the drift region; and

a second field dispersion region arranged between the drift region and the buffer region, the second field dispersion region ~~being in~~ having a same conduction type ~~same~~ as the drift region and having a low net impurity concentration.

6. (Currently Amended) A high withstand voltage field effect type semiconductor device ~~according to claim 2 further~~ comprising:

a body region arranged in a semiconductor substrate;

a gate electrode facing to the body region;

a drift region arranged below the body region in the semiconductor substrate, the drift region having a conduction type opposite to that of the body region;

a field dispersion region arranged between the body region and the drift region, the field dispersion region having a conduction type which is the same as that of the drift region and having a low net impurity concentration;

a buffer region arranged at an opposite side of the body region with the drift region arranged between the buffer region and the body region, the buffer region ~~being in~~ having a same conduction type ~~same~~ as the drift region; and

a second field dispersion region arranged between the drift region and the buffer region, the second field dispersion region ~~being in~~ having a same conduction type ~~same~~ as the drift region and having a low net impurity concentration, wherein

the gate electrode is trench-structured; and

the field dispersion region is formed extending to bottom of the gate electrode.

7. (Currently Amended) A high withstand voltage field effect type semiconductor device according to claim 3 further comprising:

a buffer region arranged at an opposite side of the body region with the drift region arranged between the buffer region and the body region, the buffer region ~~being in~~ having a same conduction type ~~same~~ as the drift region; and

a second field dispersion region arranged between the drift region and the buffer region, the second field dispersion region ~~being in~~ having a same conduction type ~~same~~ as the drift region and having a low net impurity concentration.

8. (Currently Amended) A high withstand voltage field effect type semiconductor device according to claim 4 further comprising:

a buffer region arranged at an opposite side of the body region with the drift region arranged between the buffer region and the body region, the buffer region ~~being in~~ having a same conduction type ~~same~~ as the drift region; and

a second field dispersion region arranged between the drift region and the buffer region, the second field dispersion region ~~being in~~ having a same conduction type ~~same~~ as the drift region and having a low net impurity concentration.

9. (Currently Amended) A high withstand voltage field effect type semiconductor device according to claim 5:

further comprising a collector region arranged at an opposite side of the drift region with the buffer region arranged between the collector region and the drift region,

the collector region ~~being in~~ having an opposite conduction type ~~opposite to~~ as that of the drift region; and

wherein a net impurity concentration of the buffer region is the same as or lower than half of a net impurity concentration of the collector region.

10. (Currently Amended) A high withstand voltage field effect type semiconductor device according to claim 6:

further comprising a collector region arranged at opposite side of the drift region with the buffer region arranged between the collector region and the drift region, the collector region ~~being in~~ having an opposite conduction type ~~opposite~~ to that of the drift region; and

wherein a net impurity concentration of the buffer region is the same as or lower than half of a net impurity concentration of the collector region.

11. (Currently Amended) A high withstand voltage field effect type semiconductor device according to claim 7:

further comprising a collector region arranged at an opposite side of the drift region with the buffer region arranged between the collector region and the drift region, the collector region ~~being in~~ having an opposite conduction type ~~opposite~~ to that of the drift region; and

wherein a net impurity concentration of the buffer region is the same as or lower than half of a net impurity concentration of the collector region.

12. (Currently Amended) A high withstand voltage field effect type semiconductor device according to claim 8:

further comprising a collector region arranged at opposite side of the drift region with the buffer region arranged between the collector region and the drift region, the collector region ~~being in~~ having an opposite conduction type ~~opposite~~ to that of the drift region; and

wherein a net impurity concentration of the buffer region is the same as or lower than half of a net impurity concentration of the collector region.

13. (Currently Amended) A high withstand voltage field effect type semiconductor device according to claim 5,

wherein a thickness of the buffer region is smaller than a dispersion length of minority carrier.

14. (Currently Amended) A high withstand voltage field effect type semiconductor device according to claim 6,

wherein a thickness of the buffer region is smaller than a dispersion length of minority carrier.

15. (Currently Amended) A high withstand voltage field effect type semiconductor device according to claim 7,

wherein a thickness of the buffer region is smaller than a dispersion length of minority carrier.

16. (Currently Amended) A high withstand voltage field effect type semiconductor device according to claim 9,

wherein a thickness of the buffer region is smaller than a dispersion length of minority carrier.

17. (Currently Amended) A high withstand voltage field effect type semiconductor device according to claim 10,

wherein a thickness of the buffer region is smaller than a dispersion length of minority carrier.

18. (Currently Amended) A high withstand voltage field effect type semiconductor device according to claim 11,

wherein a thickness of the buffer region is smaller than a dispersion length of minority carrier.

19. (Original) A high withstand voltage field effect type semiconductor device according to claim 5,

further comprising a carrier life time control region including at least the buffer region.

20. Cancelled.